

2.7V to 5.5V, 3A 1ch Synchronous Buck Converter with Integrated FET

BD8963EFJ

General Description

The BD8963EFJ is ROHM's high efficiency step-down switching regulator designed to produce a voltage as low as 1.0V from a supply voltage of 5.5V/3.3V. It offers high efficiency by using synchronous switches and provides fast transient response to sudden load changes by implementing current mode control.

Features

- Fast Transient Response because of Current Mode Control System
- High Efficiency for All Load Ranges because of Synchronous Switches
- Soft-Start Function
- Thermal Shutdown and UVLO Functions
- Short Circuit Current Protection with Time Delay Function
- Shutdown Function

Applications

Power Supply for LSI including DSP, Microcomputer and ASIC

Key Specifications

Input Voltage Range: 2.7V to 5.5V Output Voltage Range: 1.0V to 2.5V Average Output Current: 3.0A (Max) Switching Frequency: 1MHz (Typ) Pch FET ON-Resistance: $145m\Omega(Typ)$ $80m\Omega(Typ)$ Nch FET ON-Resistance: Standby Current: 5.0µA (Typ) **Operating Temperature Range:** -25°C to +85°C

Package

W(Typ) x D(Typ) x H(Max)



Typical Application Circuit

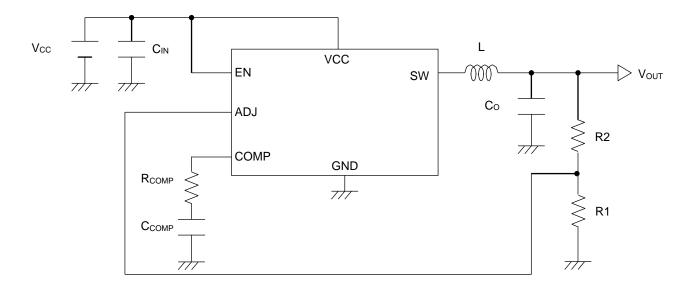


Figure 1. Typical Application Circuit

OProduct structure : Silicon monolithic integrated circuit O This product has no designed protection against radioactive rays

Pin Configuration

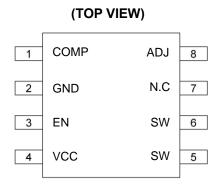


Figure 2. Pin Configuration

Pin Description

2000.100.00						
Pin No.	Pin Name	Pin Function				
1	COMP	GmAmp output pin/connected to phase compensation capacitor				
2	GND	Ground pin				
3	EN	Enable pin (Active High, Open Active)				
4	VCC	Power supply input pin				
5	SW	Power switch node				
6	SW	Power switch node				
7	N.C	No connection				
8	ADJ	Output voltage detection pin				

Block Diagram

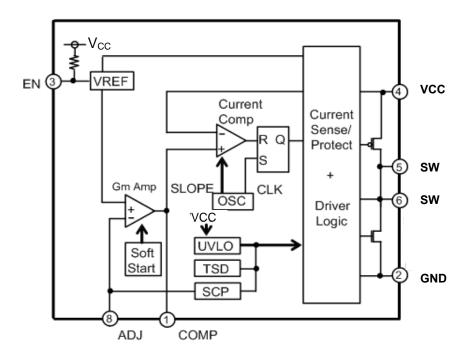


Figure 3. Block Diagram

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
VCC Voltage	Vcc	-0.3 to +7 (Note 1)	V
EN Voltage	VEN	-0.3 to +7	V
SW,COMP Voltage	Vsw,Vcomp	-0.3 to +7	V
Power Dissipation 1	Pd1	0.5 (Note 2)	W
Power Dissipation 2	Pd2	3.76 (Note 3)	W
Operating Temperature Range	Topr	-25 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Maximum Junction Temperature	Tjmax	+150	°C

⁽Note 1) Pd should not be exceeded.

Caution: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Recommended Operating Conditions (Ta=-25°C to +85°C)

Parameter	Symbol		Unit		
Farameter		Min	Тур	Max	Utill
Power Supply Voltage	Vcc	2.7 (Note 5)	5.0	5.5	V
EN Voltage	V _{EN}	0	-	Vcc	V
Output Voltage Range	Vouт	1.0	-	2.5 (Note 4)	V
SW Average Output Current	Isw	-	-	3.0 (Note 5)	Α

⁽Note 4) In case of setting the output voltage to 1.6V or more, V_{CCMin} = V_{OUT} +2.25V

Electrical Characteristics

(Unless otherwise specified , Ta=25°C V_{CC} =5 V_{VEN} = V_{CC} , R_1 =20 $k\Omega$, R_2 =7.5 $k\Omega$)

Dorometer	Symbol	Limit			l loit	Conditions
Parameter		Min	Тур	Max	Unit	Conditions
Standby Current	I _{STB}	-	5	20	μΑ	EN=GND
Bias Current	Icc	-	350	600	μΑ	
EN Low Voltage	V _{ENL}	-	GND	0.3	V	Standby mode
EN High Voltage	Venh	2.0	Vcc	-	V	Active mode
EN Current	I _{EN}	-	1.25	10	μΑ	V _{EN} =5V
Oscillation Frequency	fosc	0.8	1	1.2	MHz	
Pch FET ON-Resistance	RONP	-	145	290	mΩ	Vcc=5V
Nch FET ON-Resistance	Ronn	-	80	160	mΩ	V _{CC} =5V
ADJ Reference Voltage	V _{ADJ}	0.788	0.800	0.812	V	
COMP Sink Current	Icompsi	10	25	-	μΑ	V _{ADJ} =1.0V
COMP Source Current	Ісомрѕо	10	25	-	μΑ	V _{ADJ} =0.6V
UVLO Threshold Voltage	V _{UVLO1}	2.400	2.500	2.600	V	V _{CC} =5V to 0V
UVLO Hysteresis Voltage	V_{UVLO2}	2.425	2.550	2.700	V	V _{CC} =0V to 5V
Soft Start Time	tss	0.5	1	2	ms	
Timer Latch Time	t LATCH	1	2	4	ms	
Output Short Circuit Threshold Voltage	V _{SCP}	-	V _{ОUТ} х0.5	V _{OUT} X0.7	V	V _{OUT} =1.0V to 0V

⁽Note 2) Reduce by 4.0mW/°C for Ta above 25°C.

⁽Note 3) When mounted on a 4-layer 70.0mm x 70.0mm x 1.6mm Glass-epoxy PCB. Reduce by 30.0mW/°C for Ta above 25°C.

⁽Note 5) Pd should not be exceeded.

Typical Performance Curves

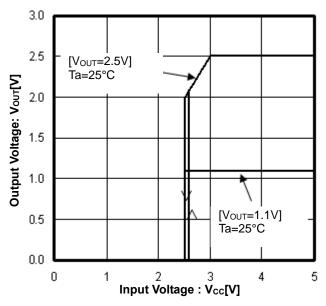


Figure 4. Output Voltage vs Input Voltage

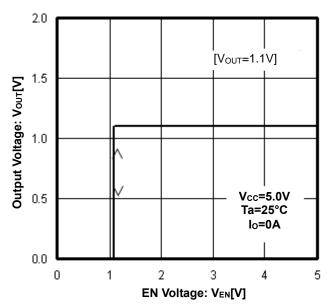


Figure 5. Output Voltage vs EN Voltage

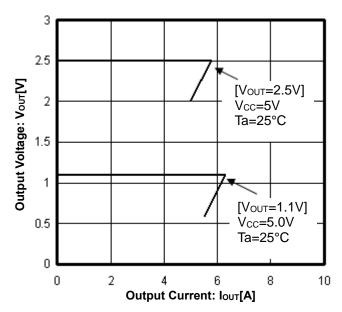


Figure 6. Output Voltage vs Output Current

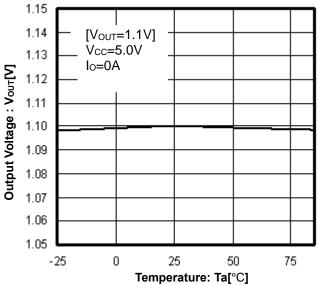


Figure 7. Output Voltage vs Temperature

Typical Performance Curves - continued

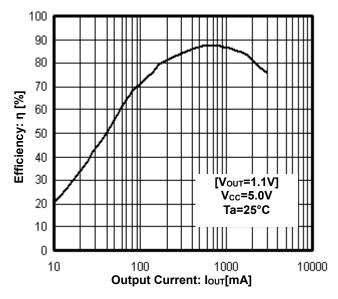


Figure 8. Efficiency vs Output Current

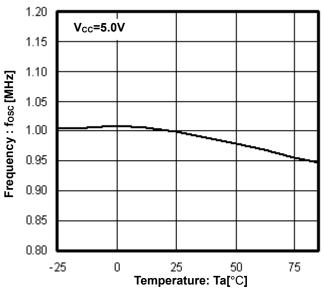


Figure 9. Frequency vs Temperature

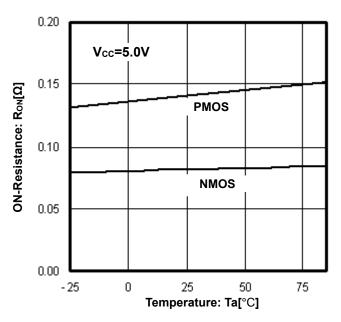


Figure 10. ON-Resistance vs Temperature

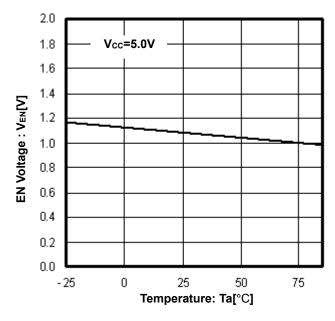


Figure 11. EN Voltage vs Temperature

Typical Performance Curves - continued

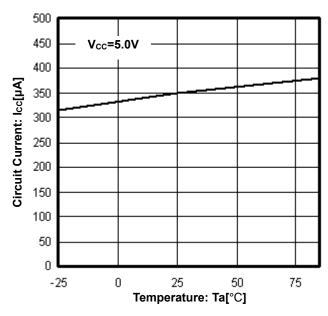


Figure 12. Circuit Current vs Temperature

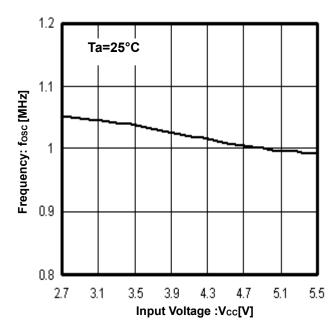


Figure 13. Frequency vs Input Voltage

Typical Waveforms

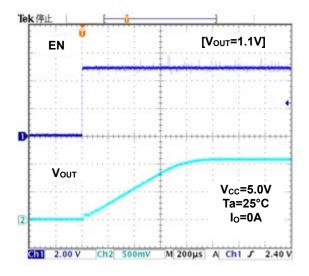


Figure 14. Soft Start Waveform

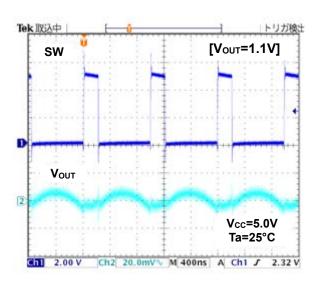


Figure 15. SW Waveform (Io=10mA)

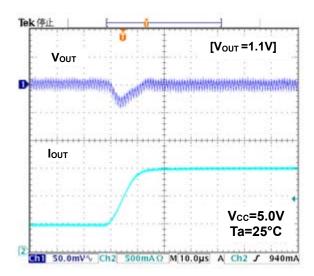


Figure 16. Transient Response (Io=0.5A to1.5A, 10µs)

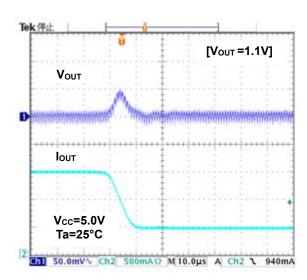


Figure 17. Transient Response (Io=1.5A to 0.5A, 10µs)

Application Information

1. Operation

(1) Synchronous Rectifier

Integrated synchronous rectification using two MOSFETs reduces power dissipation and increases efficiency when compared to converters using external diodes. Internal shoot-through current limiting circuit further reduces power dissipation.

(2) Current Mode PWM Control

PWM control signal of this IC depends on two feedback loops, the voltage feedback and the inductor current feedback.

(a) PWM (Pulse Width Modulation) Control

The clock signal coming from OSC has a frequency of 1MHz. When OSC sets the RS latch, the P-Channel MOSFET is turned ON and the N-Channel MOSFET is turned OFF. The opposite happens when the current comparator (Current Comp) resets the RS latch i.e. the P-Channel MOSFET is turned OFF and the N-Channel MOSFET is turned ON. Current Comp's output is a comparison of two signals, the current feedback control signal "SENSE" which is a voltage proportional to the current I_L, and the voltage feedback control signal, FB.

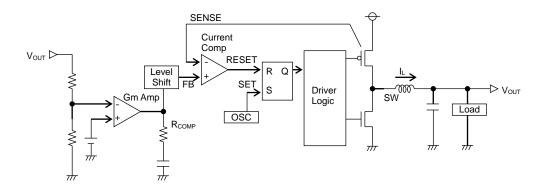


Figure 18. Diagram of Current Mode PWM Control

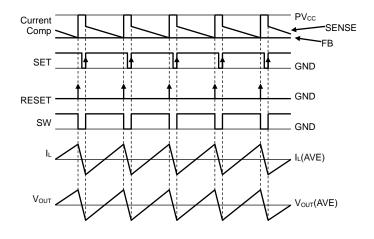


Figure 19. PWM Switching Timing Chart

2. Description of Functions

(1) Soft-Start Function

During start-up, the soft-start circuit gradually establishes the output voltage to limit the input current. This prevents the overshoot in the output voltage and inrush current.

(2) Shutdown Function

When EN terminal is "Low", the device switches to Standby Mode, and all the functional blocks including reference voltage circuit, internal oscillator and drivers are Turned OFF. Circuit current during standby is 5µA (Typ).

(3) UVLO Function

The UVLO circuit detects whether the supplied input voltage is sufficient to obtain the output voltage of this IC. The UVLO threshold has a hysteresis of 50mV (Typ) to prevent the output from chattering.

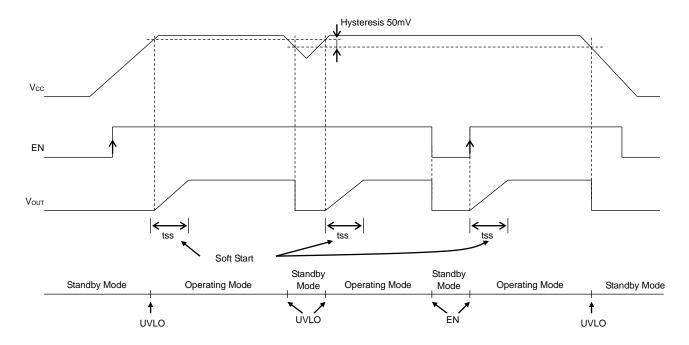


Figure 20. Soft-Start, Shutdown, UVLO Timing Chart

(4) Short Circuit Current Protection with Time Delay Function

To protect the IC from breakdown, the short circuit protection turns the output OFF when the internal current limiter is activated continuously for a fixed time (tlatch) or more. The output that is kept OFF may be turned ON again by restarting EN or by resetting UVLO.

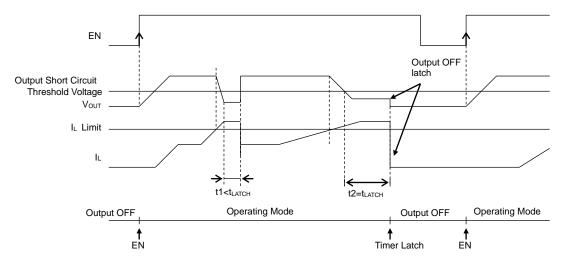


Figure 21. Short Current Protection Circuit with Time Delay Timing Chart

3. Information on Advantages

Advantage 1: Fast Transient Response with Current Mode Control System

Conventional Product (Load response Io= 0.5A to 1.5A)

BD8963EFJ (Load Response Io= 0.5A to 1.5A)

Vout

Vout

Vout

Iout

Voltage drop due to sudden change in load was reduced by about 50%.

Figure 22. Comparison of Transient Response

Advantage 2: High Efficiency for all Load Range Because of its Synchronous Rectifier

For heavier load:

This IC utilizes the synchronous rectifying mode and uses low ON-Resistance MOSFET power transistors.

ON-Resistance of P-Channel MOS FET : 145mΩ(Typ)
ON-Resistance of N-Channel MOS FET : 80mΩ(Typ)

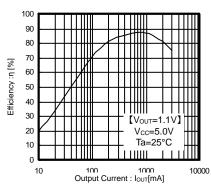


Figure 23. Efficiency

Advantage 3: • Smaller Package due to Integration of Small-Sized Power MOSFETs



- Required output capacitor, Co, for current mode control: 10µF ceramic capacitor
- Required inductance, L, for the operating frequency of 1 MHz: 1.5 μ H inductor

Reduces the required mounting area

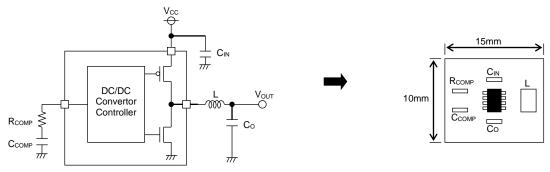


Figure 24. Example Application

4. Switching Regulator Efficiency

Efficiency η may be expressed by the equation shown below:

$$\eta = \frac{V_{OUT} \times I_{OUT}}{V_{IN} \times I_{IN}} \times 100 = \frac{P_{OUT}}{P_{IN}} \times 100 = \frac{P_{OUT}}{P_{OUT} + Pd\alpha} \times 100$$
 [%]

Efficiency may be improved by reducing the switching regulator power dissipation factors Pdα as follows:

Dissipation Factors:

(1) ON-Resistance Dissipation of Inductor and FET: Pd(I²R)

$$Pd(I^2R) = I_{OUT}^2 \times (R_{COIL} + R_{ON})$$

Where:

 R_{COIL} is the DC resistance of inductor R_{ON} is the ON-Resistance of FET I_{OUT} is the output current

(2) Gate Charge/Discharge Dissipation : Pd(Gate)

$$Pd(Gate) = C_{gs} \times f \times V^2$$

Where:

 C_{gs} is the gate capacitance of FET f is the switching frequency V is the gate driving voltage of FET

(3) Switching Dissipation: Pd(SW)

$$Pd(SW) = \frac{V_{IN}^{2} \times C_{RSS} \times I_{OUT} \times f}{I_{DRIVE}}$$

Where:

 C_{RSS} is the reverse transfer capacitance of FET I_{DRIVE} is the peak current of gate

(4) ESR Dissipation of Capacitor : Pd(ESR)

$$Pd(ESR) = I_{RMS^2} \times ESR$$

Where:

 I_{RMS} is the ripple current of capacitor ESR is the equivalent series resistance

(5) Operating Current Dissipation of IC: Pd(IC)

$$Pd(IC) = V_{IN} \times I_{CC}$$

Where:

 I_{CC} is the circuit current

5. Considerations on Permissible Dissipation and Heat Generation

Since this IC functions with high efficiency without significant heat generation in most applications, no special consideration is needed on permissible dissipation or heat generation. In case of extreme conditions, however, including lower input voltage, higher output voltage, heavier load, and/or higher temperature, the permissible dissipation and/or heat generation must be carefully considered.

For dissipation, only conduction losses due to DC resistance of inductor and ON-Resistance of FET are considered. This is because the conduction losses are most significant among other dissipation factors mentioned above including gate charge/discharge dissipation and switching dissipation.

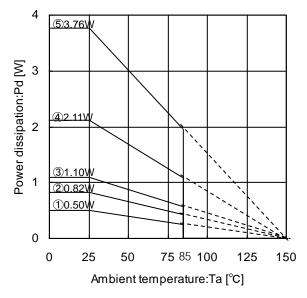


Figure 25. Thermal Derating Curve (HTSOP-J8)

① IC only
θj-a=249.5°C/W
②1 layers (copper foil area:0mm x 0mm)
θj-a=153.2°C/W
③2 layers (copper foil area:15mm x 15mm)
θj-a=113.6°C/W
④2 layers (copper foil area:70mm x 70mm)
θj-a=59.2°C/W
⑤4 layers (copper foil area:70mm x 70mm)
θj-a=33.3°C/W
(when mounted on a board 70mm x 70mm x 1.6mm
Glass-epoxy PCB with thermal Via)

$$P = I_{OUT}^{2} \times R_{ON}$$

$$R_{ON} = D \times R_{ONP} + (1 - D)R_{ONN}$$

D is the ON duty (=V_{OUT}/V_{CC}) R_{COIL} is the DC Resistance of coil R_{ONP} is the ON-Resistance of P-Channel MOS FET R_{ONN} is the ON-Resistance of N-Channel MOS FET I_{OUT} is the Output Current

 $\begin{array}{l} \text{Ex.)V}_{\text{CC}=5\text{V}, \ V_{\text{OUT}}=1.1\text{V}, \ R_{\text{ONP}}=0.145\Omega, \ R_{\text{ONN}}=0.08\Omega} \\ \text{I}_{\text{OUT}=3\text{A}, \ for \ example,} \\ \text{D=V}_{\text{OUT}/\text{V}_{\text{CC}}=1.1/5=0.22} \\ \text{R}_{\text{ON}=0.22\text{x}0.145+(1-0.22)\text{x}0.08} \\ = 0.0319+0.0624 \\ = 0.0943[\Omega] \end{array}$

P=3²x0.0943=0.8487[W]

Since R_{ONP} is greater than R_{ONN} in this IC, the dissipation increases as the on duty becomes greater. Taking into consideration the dissipation shown above, thermal design must be carried out with allowable sufficient margin.

6. Selection of Externally Connected Components

(1) Selection of Inductor (L)

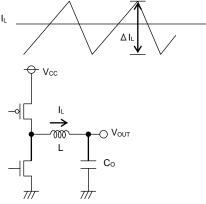


Figure 26. Output Ripple Current

The inductance significantly depends on output ripple current. As shown in equation (1), the ripple current decreases as the inductor and/or switching frequency increases.

$$\Delta I_L = \frac{\left(V_{CC} - V_{OUT}\right) \times V_{OUT}}{L \times V_{CC} \times f} \qquad \left[A\right] \quad \cdot \quad \cdot \quad (1)$$

Appropriate ripple current at output should be +/-20% of the maximum output current.

$$\Delta I_L = 0.2 \times I_{OUTMax}$$
 [A] . . . (2)

$$L = \frac{\left(V_{CC} - V_{OUT}\right) \times V_{OUT}}{\Delta I_L \times V_{CC} \times f} \qquad [H] \qquad \cdot \cdot \cdot (3)$$

Where

 ΔI_L is the Output ripple current, and f is the Switching frequency

Note: Current exceeding the current rating of the inductor results in magnetic saturation of the inductor, which decreases efficiency. The inductor must be selected to allow a sufficient margin with which the peak current may not exceed its current rating.

If V_{CC} =5V, V_{OUT} =1.1V, f=1MHz, ΔI_L =0.2A x 3A=0.6A, for example, (BD8963EFJ)

$$L = \frac{(5-1.1)\times 1.1}{0.6\times 5\times 1M} = 1.43\mu \to 1.5 \qquad [\mu H]$$

Note: Select the inductor with low resistance component (such as DCR and ACR) to minimize dissipation in the inductor for better efficiency.

(2) Selection of Output Capacitor (Co)

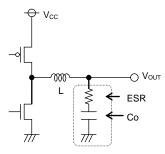


Figure 27. Output Capacitor

Output capacitor should be selected with the consideration on the stability region and the equivalent series resistance required in smoothing the ripple voltage.

Output ripple voltage is determined by equation (4):

$$\Delta V_{OUT} = \Delta I_L \times ESR$$
 [V] • • (4)

Where

 ΔI_L is the Output ripple current, and

ESR is the Equivalent series resistance of output capacitor

Note: Rating of the capacitor should be determined to allow a sufficient margin against output voltage. A 10μF to 100μF ceramic capacitor is recommended. Less ESR allows reduction in output ripple voltage.

(3) Selection of Input Capacitor (CIN)

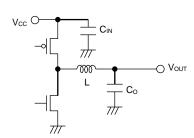


Figure 28. Input Capacitor

Input capacitor to be selected must be a low ESR capacitor with a capacitance sufficient to cope with high ripple current to prevent high transient voltage. The ripple current I_{RMS} is given by equation (5):

$$I_{RMS} = I_{OUT} \times \frac{\sqrt{V_{OUT}(V_{CC} - V_{OUT})}}{V_{CC}} \qquad [A] \cdot \cdot \cdot (5)$$

< Worst case > I_{RMSMax}

When V_{CC} is twice the V_{OUT}, $I_{RMS} = \frac{I_{OUT}}{2}$

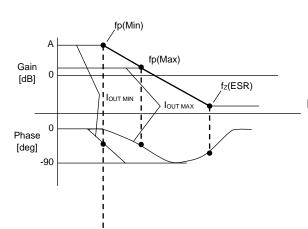
If Vcc=5V, Vout=1.1V, and IoutMax= 3A, (BD8963EFJ)

$$I_{RMS} = 3 \times \frac{\sqrt{1.1 \times (5-1.1)}}{5} \approx 1.24 \qquad [A_{RMS}]$$

A low ESR $22\mu F/10V$ ceramic capacitor is recommended to reduce ESR dissipation of input capacitor for better efficiency.

(4) Calculating RCOMP, CCOMP for Phase Compensation

Since the Current Mode Control is designed to limit the inductor current, a pole (phase lag) appears in the low frequency area due to CR filter consisting of an output capacitor and a load resistance, while a zero (phase lead) appears in the high frequency area due to the output capacitor and its ESR. Therefore, the phases are easily compensated by adding a zero to the power amplifier output with C and R as described below to cancel a pole at the power amplifier.



$$f_P = \frac{1}{2\pi \times R_O \times C_O}$$

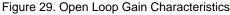
$$f_Z(ESR) = \frac{1}{2\pi \times ESR \times C_O}$$

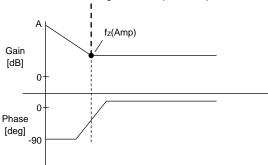
Pole at Power Amplifier

When the output current decreases, the load resistance Ro increases and the pole frequency decreases.

$$fp(Min) = \frac{1}{2\pi \times R_{OMax} \times Co}$$
 [Hz] \leftarrow with lighterload

$$fp(Max) = \frac{1}{2\pi \times R_{OMin} \times CO}$$
 [Hz] \(\sim \text{with heavier load} \)





Zero at Power Amplifier

Increasing the capacitance of the output capacitor lowers the pole frequency while the zero frequency does not change. (This is because when the capacitance is doubled, the capacitor ESR is reduced to half.)

$$f_Z(Amp) = \frac{1}{2\pi \times R_{COMP} \times C_{COMP}}$$

Figure 30. Error Amp Phase Compensation Characteristics

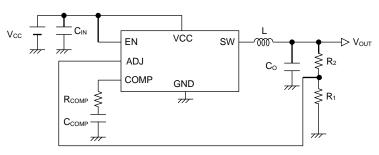


Figure 31. Typical Application

Stable feedback loop may be achieved by canceling the pole fp (Min) produced by the output capacitor and the load resistance with CR zero correction by the error amplifier.

$$f_Z(Amp) = fp(Min)$$

$$\to \frac{1}{2\pi \times R_{COMP} \times C_{COMP}} = \frac{1}{2\pi \times R_{OMax} \times C_O}$$

(5) Setting the Output Voltage

The output voltage V_{OUT} is determined by the equation (6):

$$V_{OUT} = (R_2 / R_1 + 1) \times V_{ADJ} \qquad \cdot \cdot \cdot (6)$$

Where:

V_{ADJ} is the Voltage at ADJ terminal (0.8V Typ)

The required output voltage may be determined by adjusting R₁ and R₂.

Adjustable output voltage range: 1.0V to 2.5V

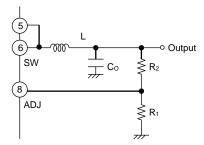


Figure 32. Determination of Output Voltage

Use 1 $k\Omega$ to 100 $k\Omega$ resistor for R_1 . When using a resistor having a resistance higher than 100 $k\Omega$, check the setup carefully for ripple voltage etc.

The lower limit of input voltage depends on the output voltage. Basically, it is recommended to use the given condition:

$$V_{CCMin} = V_{OUT} + 2.25V$$

Figure 33. shows the necessary output current value at the lower limit of input voltage. (DCR of inductor: $0.05\Omega)$

These data show characteristic value of the IC. It doesn't guarantee the operating range.

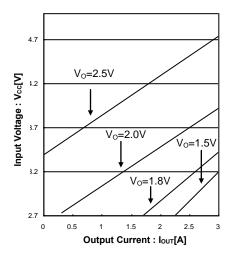


Figure 33. Minimum Input Voltage in each Output Voltage

7. BD8963EFJ Cautions on PC Board Layout

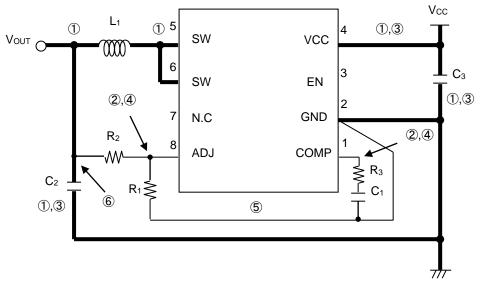
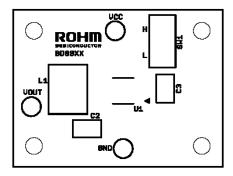


Figure 34. Layout Diagram

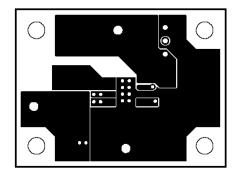
- ① To avoid conduction loss, please keep the thick Black lines as short and thick as possible.
- ② Don't place close to the switching current loop.
- 3 As close to IC pin as possible.
- 4 Keep PCB traces as short as possible.
- ⑤ Use a single point ground structure to connect with Pin2.
- 6 As close to R2 and C2 as possible.

Note: HTSOP-J8 (BD8963EFJ) has a thermal PAD on the reverse of the package.

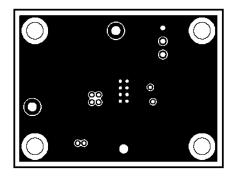
The package thermal performance may be enhanced by bonding the PAD to GND plane which occupies a large area of PCB.



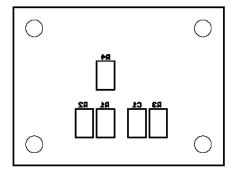
Top Silkscreen Overlay



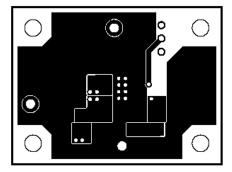
Top Layer



Middle Layer



Bottom Silkscreen Overlay



Bottom Layer

Figure 35. Reference PCB Layout Pattern

8. Recommended Components List for above Application

Symbol	Part	Value		Manufacturer	Series
L	Coil	1.5µH		TDK	VLC6045T-1R5N
Cin C	Cararia Canasitar	V _{CC} -V _{OUT} >3V	10μF	Kyocera	CM316X5R106M10A
	Ceramic Capacitor	Vcc-Vout<3V	22µF	Kyocera	CM32X5R226M10A
Co	Ceramic Capacitor	10µF		Kyocera	CM316X5R106M10A
		V _{OUT} =1.0V	330pF	Murata	GRM18 Series
	Ceramic Capacitor	Vout=1.1V	330pF	Murata	GRM18 Series
Ссомр		V _{OUT} =1.2V	330pF	Murata	GRM18 Series
		V _{OUT} =1.5V	390pF	Murata	GRM18 Series
		Vout=1.8V	390pF	Murata	GRM18 Series
		V _{OUT} =2.5V	390pF	Murata	GRM18 Series
Rcomp	Resistance	Vout=1.0V	2kΩ	Rohm	MCR03 Series
		Vout=1.1V	2kΩ	Rohm	MCR03 Series
		V _{OUT} =1.2V	2.4kΩ	Rohm	MCR03 Series
		V _{OUT} =1.5V	2.4kΩ	Rohm	MCR03 Series
		V _{OUT} =1.8V	3.6kΩ	Rohm	MCR03 Series
		V _{OUT} =2.5V	5.6kΩ	Rohm	MCR03 Series

Note: The parts list presented above is an example of recommended parts. Although the parts are standard, actual circuit characteristics should be checked on your application carefully before use. Be sure to allow sufficient margins to accommodate variations between external devices and this IC when employing the depicted circuit with other circuit constants modified. Both static and transient characteristics should be considered in establishing these margins.

I/O Equivalent Circuit

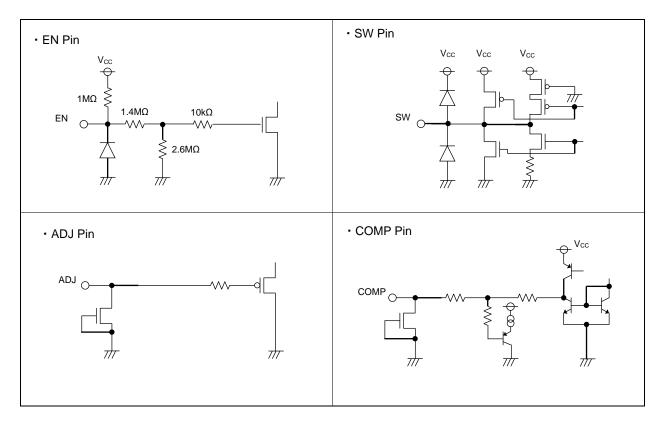


Figure 36. I/O Equivalent Circuit

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Thermal Consideration

Should by any chance the power dissipation rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the Pd rating.

6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IC can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

7. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

8. Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

9. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

10. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

Operational Notes - continued

11. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

12. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

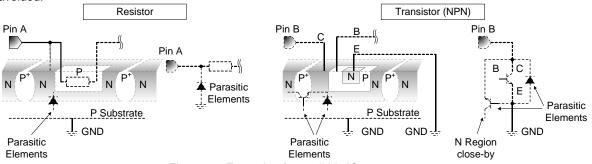


Figure 37. Example of monolithic IC structure

13. Thermal Shutdown Circuit(TSD)

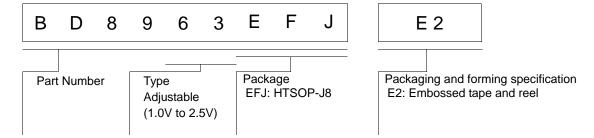
This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's power dissipation rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF all output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

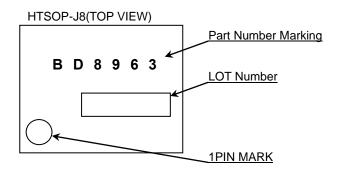
14. Selection of Inductor

It is recommended to use an inductor with a series resistance element (DCR) 0.1Ω or less. Especially, note that use of a high DCR inductor will cause an inductor loss, resulting in decreased output voltage. Should this condition continue for a specified period (soft start time + timer latch time), output short circuit protection will be activated and output will be latched OFF. When using an inductor over 0.1Ω , be careful to ensure adequate margins for variation between external devices and this IC, including transient as well as static characteristics. Furthermore, in any case, it is recommended to start up the output with EN after supply voltage is within.

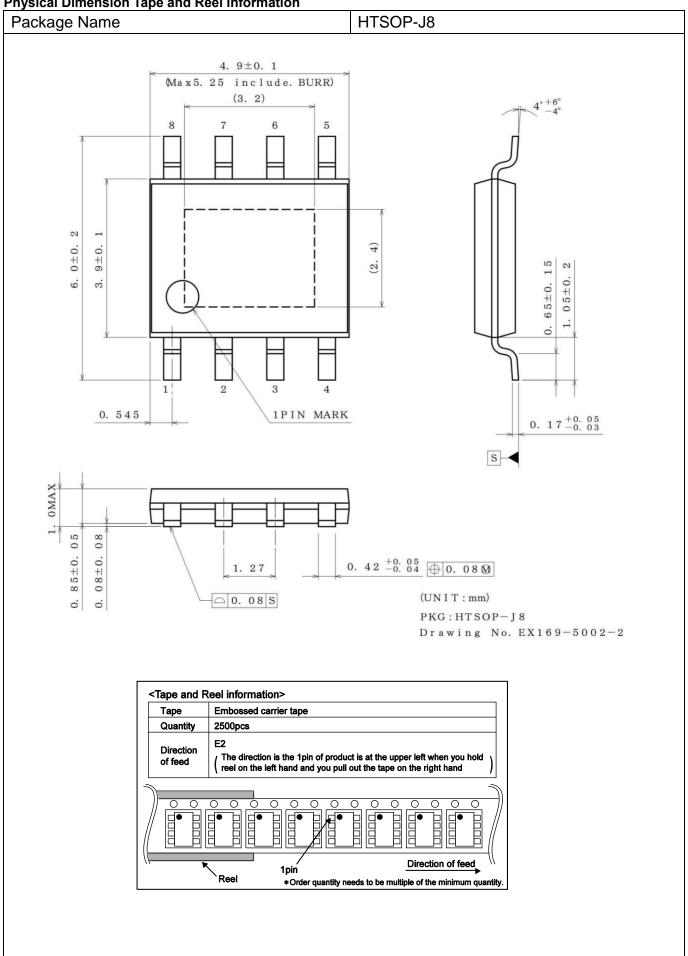
Ordering Information



Marking Diagram



Physical Dimension Tape and Reel Information



Revision History

Date	Revision	Changes			
17.Jan.2012	001	New Release			
13.May.2014	002	19/24 page I/O Equivalence circuit (EN pin I/O Equivalence Circuit is revised.)			
02.Oct.2014	003	Applied the ROHM Standard Style and improved understandability.			

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CLASSIV	CLASSII	CLASSⅢ	CLASSⅢ	

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 - [h] Use of the Products in places subject to dew condensation
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- Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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